

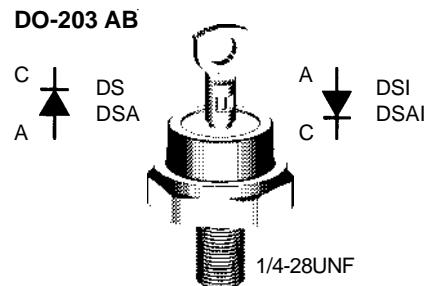
Rectifier Diode

Avalanche Diode

V_{RRM} = 800-1800 V
I_{F(RMS)} = 80 A
I_{F(AV)M} = 49 A

V _{RSM} V	V _{(BR)min} V	V _{RRM} V	Anode on stud	Cathode on stud
900	-	800	DS 35-08A	DSI 35-08A
1300	-	1200	DS 35-12A	DSI 35-12A
1300	1300	1200	DSA 35-12A	DSA 35-12A
1700	1750	1600	DSA 35-16A	DSA 35-16A
1900	1950	1800	DSA 35-18A	DSA 35-18A

^① Only for Avalanche Diodes

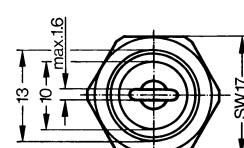
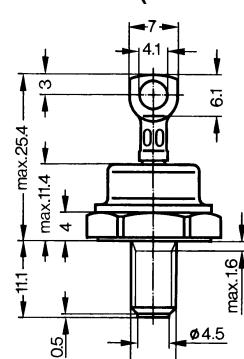


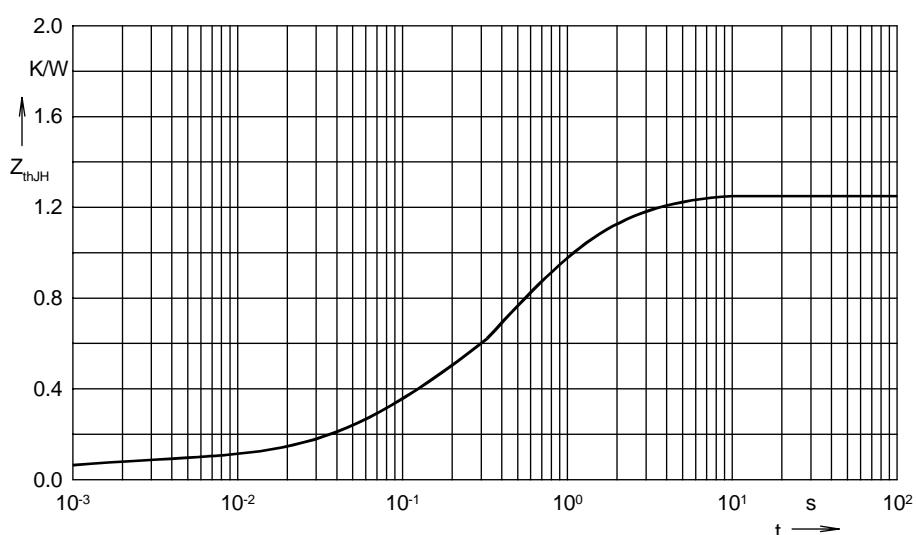
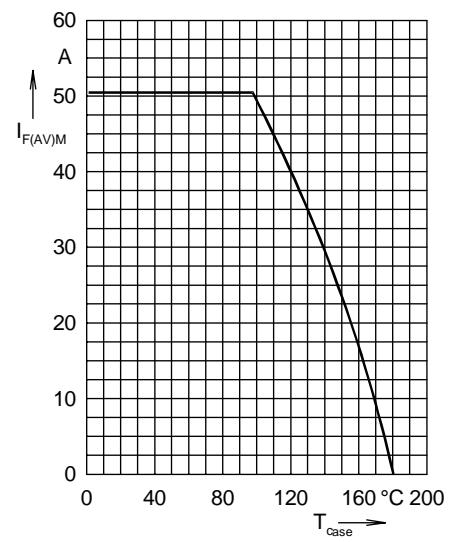
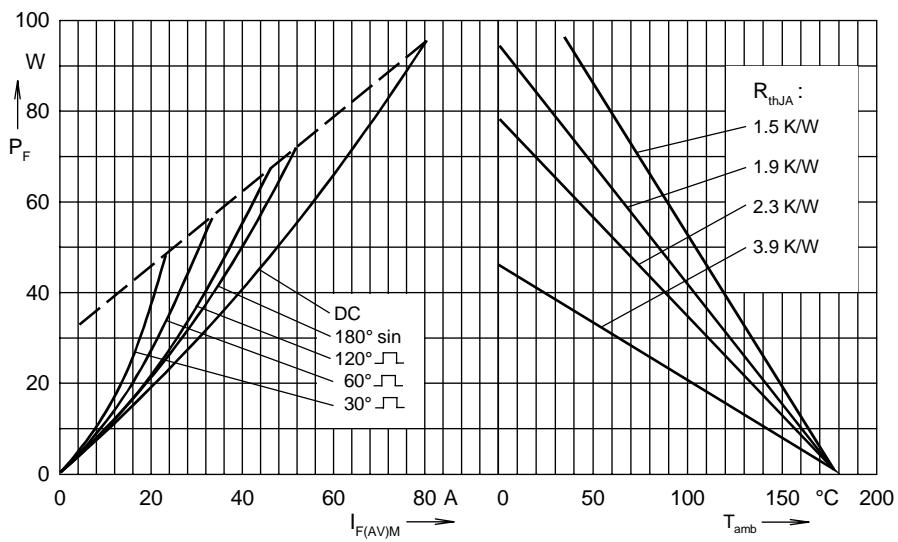
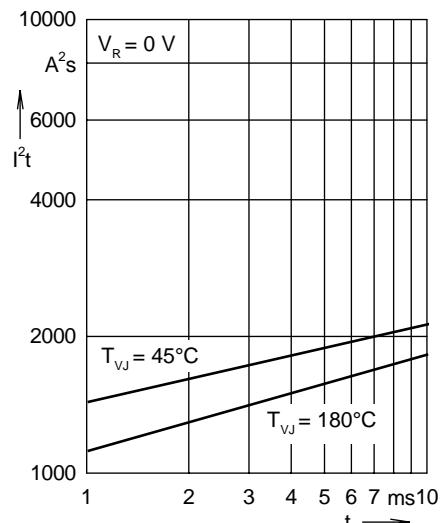
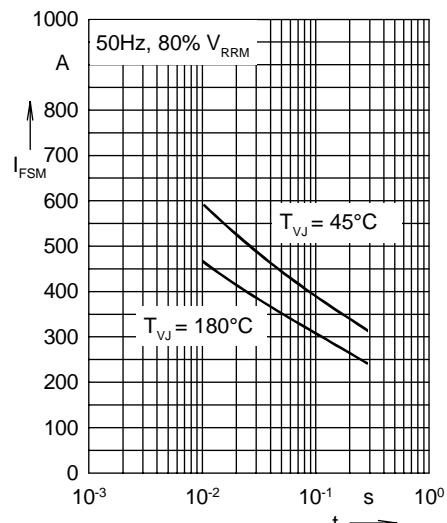
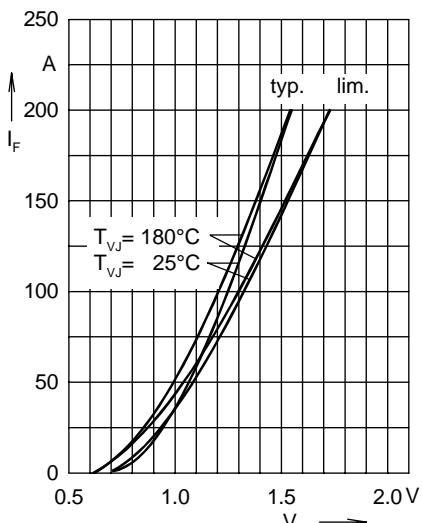
A = Anode C = Cathode

Symbol	Test Conditions	Maximum Ratings		
I _{F(RMS)}	T _{VJ} = T _{VJM}	80	A	
I _{F(AV)M}	T _{case} = 100°C; 180° sine	49	A	
P _{RSM}	DSA(I) types, T _{VJ} = T _{VJM} , t _p = 10 µs	11	kW	
I _{FSM}	T _{VJ} = 45°C; V _R = 0	650 690	A A	
	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine			
	T _{VJ} = T _{VJM} V _R = 0	600 640	A A	
	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine			
I ² t	T _{VJ} = 45°C V _R = 0	2100 2000	A ² s A ² s	
	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine			
	T _{VJ} = T _{VJM} V _R = 0	1800 1700	A ² s A ² s	
	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine			
T _{VJ}		-40...+180	°C	
T _{VJM}		180	°C	
T _{stg}		-40...+180	°C	
M _d	Mounting torque	4.5-5.5 40-49	Nm lb.in.	
Weight		15	g	

Symbol	Test Conditions	Characteristic Values		
I _R	T _{VJ} = T _{VJM} ; V _R = V _{RRM}	≤ 4	mA	
V _F	I _F = 150 A; T _{VJ} = 25°C	≤ 1.55	V	
V _{TO}	For power-loss calculations only	0.85	V	
r _T	T _{VJ} = T _{VJM}	4.5	mΩ	
R _{thJC}	DC current	1.05	K/W	
R _{thJH}	DC current	1.25	K/W	
d _S	Creepage distance on surface	4.05	mm	
d _A	Strike distance through air	3.9	mm	
a	Max. allowable acceleration	100	m/s ²	

Data according to IEC 60747
 IXYS reserves the right to change limits, test conditions and dimensions





R_{thJH} for various conduction angles d:

d	R_{thJH} (K/W)
DC	1.25
180°	1.37
120°	1.47
60°	1.74
30°	2.08

Constants for Z_{thJH} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.10	0.0012
2	0.25	0.1181
3	0.70	0.6540
4	0.20	2.0